## AUTHOR INDEX


Abernathey, J.R., D.W. Greenwell and F. Rosenberger, Congruent (diffusionless) vapor transport 47 (1979) 145
Aguiló, M., see Rodriguez 47 (1979) 518
Anzai, H., Growth of large crystals of tetramethyltetrathiafulvalenium tetracyanoquinodimethanide (TMTTF-TCNQ) 47 (1979) 733
Aquilano, D., see Franchini-Angela 47 (1979) 719
Arend, H., see Lefaucheux 47 (1979) 313
Astles, M.G., P. Hatto and A.J. Crocker, Liquidus measurements in the Pb–Sn–Te system 47 (1979) 379
Azouni, M.A., Local temperature measurements over ice-water interface and convective flow patterns 47 (1979) 109

Balchin, A.A., see Whitehouse 47 (1979) 203
Bannai, E., see Yajima 47 (1979) 493
Bartels, G., D. Mateika and J.M. Robertson, Preparation of barium lead hexa-aluminate single crystal layers by the liquid phase epitaxy technique 47 (1979) 414
Barter, B.H., I.M. Boswarva, D.B. Holt, J.H.E. Jeffes and J.B. Steyn, Growth of films of CdS evaporated in vacuum onto silicon 47 (1979) 623
Bartlett, B.E., P. Capper, J.E. Harris and M.J.T. Quelch, A study of casting in the $Cd_xHg_{1-x}Te$ system 47 (1979) 341
Bass, S.J., Silicon and germanium doping of epithaxial gallium arsenide grown by the trimethylgallium-arsine method 47 (1979) 613
Bensahel, D., M. Dupuy and J.C. Pfister, Transmission electron microscopy observations of precipitates in ZnTe: shape of the tellurium solidus line 47 (1979) 727
Berger, R.S., see Brun 47 (1979) 335
Bernardini, J.E., see Wernick 47 (1979) 73
Berthon, J., A. Revcolevschi, H. Morikawa and B. Touzelin, Growth of wustite ($Fe_{1-x}O$) crystals of various stoichiometries 47 (1979) 736
Bhalla, A.S., see Brun 47 (1979) 335
Bhoskar, B.T., see Joshi 47 (1979) 654
Billia, B. et L. Capella, Stabilité morphologique de la croissance unidirectionelle avec interface plane d'un monocristal d'alliage binarire dilué; étude en thermodynamique non linéaire des processus irréversibles 47 (1979) 261
Billia, B., see Coulet 47 (1979) 469
Bloem,J., see Rijks 47 (1979) 397
Bloem, J., see Putte 47 (1979) 437
Boncheva-Mladenova, Z. and N. Dishovsky, Growth of $Bi_2(SeO_4)_3$ single crystals in silica gels 47 (1979) 82
Boncheva-Mladenova, Z. and N. Dishovsky, Growth of single crystals of $Ag_2SeO_4$ in silica gels 47 (1979) 467
Boswarva, I.M., see Barter 47 (1979) 623
Botsaris, G.D., see Wormer 47 (1979) 127
Bressel, B., B. Chevalier, J. Etourneau and P. Hagenmuller, Czochralski crystal growth of rare earth tetraborides 47 (1979) 429
Brun, M.K., A.S. Bhalla, K.E. Spear, L.E. Cross and R.S. Berger, Crystal growth and characterization of lithium metasilicate 47 (1979) 335
Buehler, E., see Wernick 47 (1979) 73

Camel, D., C. Lemaignan and J. Pélissier, In-situ observation of solidification interfaces with a very high voltage electron microscope 47 (1979) 317
Capella, L., see Billia 47 (1979) 261
Capella, L., see Coulet 47 (1979) 469
Capper, P., see Bartlett 47 (1979) 341
Champier, G., see Sekiguchi 47 (1979) 751
Chen, P.S., P.J. Shlichta, W.R. Wilcox and R.A. Lefever, Convection phenomena during the growth of sodium chlorate crystals from solution 47 (1979) 43

Chevalier, B., see Bressel 47 (1979) 429
Chevrier, J., A. Huber and N.T. Linh, Vapour phase epitaxy of InP: Growth kinetics and controlled doping 47 (1979) 267
Christoffersen, J., M.R. Christoffersen, G.M. van Rosmalen and W.G.J. Marchée, The affinity of crystal growth and dissolution in aqueous solution with special reference to calcium sulphate dihydrate 47 (1979) 607
Christoffersen, M.R., see Christoffersen 47 (1979) 607
Christoffersen, J., and M.R. Christoffersen, Kinetics of dissolution of calcium hydroxyapatite, II. Dissolution in non-stoichiometric solutions at constant pH 47 (1979) 671
Christoffersen, M.R., see Christoffersen 47 (1979) 671
Clyne, T.W., Theoretical solute redistribution during a modified form of zone refining – cascade purification 47 (1979) 85
Coulet, A.L., B. Billia et L. Capella, Observation par attaque chimique et topographie X des structures cellulaires de monocristaux d'alliages métalliques binaires dilués 47 (1979) 469
Courbion, G., see Plet 47 (1979) 699
Crocker, A.J., see Astles 47 (1979) 379
Cross, L.E., see Brun 47 (1979) 335
Cutter, J.R. and J. Woods, Growth of single crystals of zinc selenide from the vapour phase 47 (1979) 405

Damen, J.P.M., J.M. Robertson and M.A.H. Huyberts, Thin film growth of $(Mn_xZn_{1-x})Fe_2O_4$ by liquid phase epitaxy on Bridgman grown $Zn_2TiO_4$ substrates 47 (1979) 486
Danilowicz, R., L. Kanney and R.D. Etters, Thermodynamic bahvior of small $Cl^-Ar_{N-1}$ ionic clusters 47 (1979) 164
Davey, R.J., R.I. Ristić and B. Zizić, The role of dislocations in the growth of ammonium dihydrogen phosphate crystals from aqueous solutions 47 (1979) 1
Delong, M.C., see Rosenberger 47 (1979) 321
De Pape, R., see Plet 47 (1979) 699
Dillin, D.R., see Mullica 47 (1979) 635
Dishovsky, N., see Boncheva-Mladenova 47 (1979) 82
Dishovsky, N., see Boncheva-Mladenova 47 (1979) 467
Down, M.G. and R.J. Pulham, Low temperature method for the growth of lithium nitride single crystals 47 (1979) 133
Drofenik, M., L. Golič and D. Kolar, Crystal growth of some alkaline-earth rare-earth pentaoxometallates 47 (1979) 739
Dupuy, M., see Bensahel 47 (1979) 727
Dyer, L.D., Dislocation-free Czochralski growth of ⟨110⟩ silicon crystals 47 (1979) 533

Eidelman, N., see Sarig 47 (1979) 365
Etourneau, J., see Bressel 47 (1979) 429
Etters, R.D., see Danilowicz 47 (1979) 164
Eyer, A., R. Nitsche and H. Zimmermann, A double-ellipsoid mirror furnace for zone crystallization experiments in Spacelab 47 (1979) 219

Fabian, W., see Lentz 47 (1979) 121
Fourquet, J.L., see Plet 47 (1979) 699
Franchini-Angela, M. and D. Aquilano, Growth morphology of weddellite $CaC_2O_4 \cdot 2x\ H_2O$ 47 (1979) 719
Franke, H., see Trivedi 47 (1979) 389
Frost, R.T., see Racette 47 (1979) 384
Fujita, S., H. Mimoto, H. Takebe and T. Noguchi, Growth of cubic ZnS, ZnSe and $ZnS_xSe_{1-x}$ single crystals by iodine transport 47 (1979) 326
Funakubo, H., see Sekiguchi 47 (1979) 751

Galli, E., see Majni 47 (1979) 583
Gallily, I., see Michaeli 47 (1979) 291
Garrard, B.J. and B.M. Wanklyn, Flux growth of some fluoride crystals under reducing conditions. IV 47 (1979) 159
Gautier, P., see Joullié 47 (1979) 100
Geballe, T.H., see Wernick 47 (1979) 73
Gerbaux, X. and A. Hadni, Applicability of the epitaxial nucleation in submicroscopic holes (ENSH) method to vapour growth: preparation of oriented thin films of naphthalene, durene, benzoic acid and tellurium 47 (1979) 593
Giling, L.J., see Rijks 47 (1979) 397
Giling, L.J., see Putte 47 (1979) 437
Gill, G.P., see Wilkins 47 (1979) 299
Gokieli, B., see Sokołowski 47 (1979) 421

Gołacki, Z. and J. Makowski, Crystallization of HgCdTe mixed crystals from the vapour phase by chemical transport 47 (1979) 749
Golič, L., see Drofenik 47 (1979) 739
Grange, Y., see Le Gal 47 (1979) 449
Greenwell, D.W., see Abernathey 47 (1979) 145
Griffith, W.T., On the transition from faceted to non-faceted growth in melt-grown crystals 47 (1979) 473

Hada, T., see Hata 47 (1979) 171
Hadni, A., see Gerbaux 47 (1979) 593
Hagenmuller, P., see Bressel 47 (1979) 429
Handa, V.K., see Roy 47 (1979) 577
Harris, J.E., see Bartlett 47 (1979) 341
Hata, T., T. Minamikawa, O. Morimoto and T. Hada, DC reactive magnetron sputtered ZnO films 47 (1979) 171
Hatano, T., see Osaka 47 (1979) 527
Hatto, P., see Astles 47 (1979) 379
Heinemann, K., M.J. Yacamán, C.Y. Yang and H. Poppa, The structure of small, vapor-deposited particles. I. Experimental study of single crystals and particles with pentagonal profiles 47 (1979) 177
Heinemann, K., see Yacamán 47 (1979) 187
Heinemann, K., see Yang 47 (1979) 283
Heyraud, J.C., see Métois 47 (1979) 357
Hodorowicz, S.A. and E.B. Treivus, The growth of kinetics of urea monocrystals from aqueous solution 47 (1979) 573
Holt, D.B., see Barter 47 (1979) 623
Hosoya, S., see Kitamura 47 (1979) 93
Huber, A., see Chevrier 47 (1979) 267
Hull, G.W., see Wernick 47 (1979) 73
Huyberts, M.A.H., see Damen 47 (1979) 486

Immorlica, Jr., A.A., see Ludington 47 (1979) 619
Inokuchi, K., see Nishizawa 47 (1979) 434
Isaacs, T.J. and G.W. Roland, Crystal growth of $Tl_3VS_4$ 47 (1979) 712
Ito, M., see Yoshikawa 47 (1979) 230
Ito, S., N. Yoneda, S. Shimada, A. Tsunashima, K. Kodaira and T. Matsushita, Vapor growth of $Zn_2GeO_4$ single crystals 47 (1979) 310
Itoh, H., see Takahashi 47 (1979) 245
Ittyachen, M.A., see Kurien 47 (1979) 743
Iwanaga, H., T. Yoshiie, T. Yamaguchi and N. Shibata, Crystal growth and sublimation in II–VI compounds along their polar axis 47 (1979) 703
Iwasaki, H., see Miyazawa 47 (1979) 351
Izumi, F., H. Kodama and A. Ono, Growth of anatase ($TiO_2$) crystals by chemical transport reactions with HBr and HCl 47 (1979) 139

Jeffes, J.H.E. see Barter 47 (1979) 623
Jones, K.A., The lattice mismatch between (112) chalcopyrite films and (0001) CdS substrates 47 (1979) 235
Jørgensen, J.-E. and S.E. Rasmussen, Growth of chromium silicide, $Cr_3Si$, crystals 47 (1979) 124
Joshi, M.S. and B.T. Bhoskar, Growth of fibrous sodium aluminosilicate crystals in silica gel 47 (1979) 654
Joullié, A., P. Gautier and E. Monteil, The Al–Ga–Sb ternary phase diagram and its application to solution growth 47 (1979) 100

Kadečková, S., see Vaněk 47 (1979) 458
Kajiwara, K., see Kaneko 47 (1979) 155
Kaneko, K., H. Nagasawa and K. Kajiwara, Toroidal defect at the heterointerface between GaAs and $Al_xGa_{1-x}As$ epitaxial layer 47 (1979) 155
Kanney, L., see Danilowicz 47 (1979) 164
Kato, Y., Y. Mori and K. Morizane, Chromium-doped GaAs vapor phase epitaxy 47 (1979) 12
Kawai, S., see Yajima 47 (1979) 493
Kitamura, M., S. Hosoya and I. Sunagawa, Re-investigation of the re-entrant corner effect in twinned crystals 47 (1979) 93
Kliya, M.O. and V.D. Osica, Crystals of CTA–DNA: a growth and morphological study 47 (1979) 639

Kodaira, K., see Ito 47 (1979) 310
Kodama, H., see Izumi 47 (1979) 139
Koizumi, H., see Miyazawa 47 (1979) 351
Kojima, T., I. Nishida and T. Sakata, Crystal growth of $Mn_{15}Si_{26}$ 47 (1979) 589
Kolar, D., see Drofenik 47 (1979) 739
Komeno, J., K. Kitahara and S. Ohkawa, Growth of high resistivity GaAs VPE layers for device applications by the $AsCl_3$–Ga–$N_2$ system 47 (1979) 601
Kubodera, K., see Miyazawa 47 (1979) 351
Kuiken, H.K. and P.J. Roksnoer, Analysis of the temperature distribution in FZ silicon crystals 47 (1979) 29
Kurien, K.V. and M.A. Ittyachen, Growth kinetics and habit modification of barium molybdate single crystals in silica gel 47 (1979) 743
Kuroda, E. and T. Saitoh, Growth and characterizaton of polycrystalline silicon ingots from metallurgical grade source material 47 (1979) 251

Lacmann, R., see Trivedi 47 (1979) 389
Lam, S.-T. and Z.A. Munir, Surface charge and ledge dynamics in cadmium sulfide 47 (1979) 373
Lampert, B. and K. Reichelt, Anisotropy of round evaporation spirals on rocksalt surfaces 47 (1979) 77
Leblanc, M., see Plet 47 (1979) 699
Leci, C.L., see Sarig 47 (1979) 365
Lefaucheux, F., M.C. Robert and H. Arend, Crystal quality of gel grown $CaHPO_4$, 2 $H_2O$ crystals 47 (1979) 313
Lefever, R.A., see Chen 47 (1979) 43
Le Gal, H. and Y. Grange, Crystal growth by the thermic screen translation (TST) technique; a modified Bridgeman method 47 (1979) 449
Leiss, M., see Lutz 47 (1979) 130
Lemaignan, C., see Camel 47 (1979) 317
Lentz, A. und W. Fabian, Einkristallzüchtung von Tripelnitriten in Gelen 47 (1979) 121
Linh, N.T., see Chevrier 47 (1979) 267
Ludington, B.W. and A.A. Immorlica, Jr., Temperature gradient measurement in liquid epitaxial growth systems 47 (1979) 619
Lutz, F., M. Leiss and J. Müller, Epitaxy of $NdAl_3(BO)_4$ for thin film miniature lasers 47 (1979) 130

Majini, G., G. Ottaviani and E. Galli, AuAl compound formation by thin film interactions 47 (1979) 583
Makowski, J., see Gołacki 47 (1979) 749
Marchée, W.G.J., see Christoffersen 47 (1979) 607
Mateika, D., see Bartels 47 (1979) 414
Matsushita, T., see Ito 47 (1979) 310
Métois, J.J. and J.C. Heyraud, Surface decoration: depletion zone analysis along the steps 47 (1979) 357
Meyer, H.J., Wachstumsgeschwindigkeit von Calcit aus wässerigen Lösungen 47 (1979) 21
Michaeli, G. and I. Gallily, Mass growth measurements of freely falling ice crystals produced by two different seeding methods 47 (1979) 291
Michalski, A., see Sokołowski 47 (1979) 421
Mikkelsen, Jr., J.C., Bridgman–Stockbarger crystal growth of $Li_2Ti_3O_7$ 47 (1979) 659
Milligan, W.O., see Mullica 47 (1979) 635
Mimoto, H., see Fujita 47 (1979) 326
Minamikawa, T., see Hata 47 (1979) 171
Miyazawa, S., H. Koizumi, K. Kubodera and H. Iwasaki, Epitaxial growth of $KNdP_4O_{12}$ laser waveguides 47 (1979) 351
Miyazawa, S., see Nakano 47 (1979) 693
Monteil, E., see Joullié 47 (1979) 100
Mori, Y., see Kato 47 (1979) 12
Morikawa, H., see Berthon 47 (1979) 736
Morimoto, O., see Hata 47 (1979) 171
Morizane, K., see Kato 47 (1979) 12
Müller, J., see Lutz 47 (1979) 130
Mullica, D.F., W.O. Milligan and D.R. Dillin, Aging studies on hydrous lutetium oxide 47 (1979) 635
Munir, Z.A., see Lam 47 (1979) 373

Nagasawa, H., see Kaneko 47 (1979) 155
Nakano, J., T. Yamada and S. Miyazawa, Top-seeded flux growth of $LiNdP_4O_{12}$ single crystals 47 (1979) 693
Nalbandyan, A.G., H.G. Nalbandyan and R.O. Sharkhatunyan, Enantiomorphism of $\alpha$-$LiIO_3$ single crystals 47 (1979) 427
Nalbandyan, H.G., see Nalbandyan 47 (1979) 427
Nishida, I., see Kojima 47 91979) 589
Nishizawa, J., Y. Oyama, H. Tadano, K. Inokuchi and Y. Okuno, Observations of defects in LPE GaAs revealed by new chemical etchant 47 (1979) 434
Nitsche, R., see Eyer 47 (1979) 219
Noguchi, T., see Fujita 47 (1979) 326

Ohta, M., M. Tsutsumi and S. Ueno, Observations of etch pits on as-grown faces of brushite crystals 47 (1979) 135
Oka, K., H. Unoki and T. Sakudo, Growth of single crystals of lead monoxide 47 (1979) 568
Okuda, H., see Sekiya 47 (1979) 551
Okuno, Y., see Nishizawa 47 (1979) 434
Olson, J.M., see Rosenberger 47 (1979) 321
Ono, A., see Izumi 47 (1979) 139
Osaka, T., J. Satoh, T. Hatano and K. Sakaguchi, Epitaxial growth of tin thin films on a potassium chloride substrate 47 (1979) 527
Osica, V.D., see Kliya 47 (1979) 639
Ottaviani, G., see Majni 47 (1979) 583
Oyama, Y., see Nishizawa 47 (1979) 434

Parker, R.P. and W.S. Wilson, Dimensional instability of creamed TNT 47 (1979) 5
Parry, M.A. and B.W. Thorpe, The role of HNS in the grain modification of TNT 47 (1979) 541
Patel, A.R. and A. Venkateswara Rao, Gel growth and perfection of orthorhombic potassium perchlorate single crystals 47 (1979) 213
Pélissier, J., see Camel 47 (1979) 317
Pfister, J.C., see Bensahel 47 (1979) 727
Plet, F., J.L. Fourquet, G. Courbion, M. Leblanc et R. De Pape, Croissance cristalline par voie hydrothermale en presence d'acide fluorhydrique dans les systèmes $MF-AlF_3$ ET $NH_4F-FeF_3$ 47 (1979) 699
Poppa, H., see Heinemann 47 (1979) 177
Poppa, H., see Yacamán 47 (1979) 187
Pulham, R.J., see Down 47 (1979) 133

Quelch, M.J.T., see Bartlett 47 (1979) 341

Racette, G.W. and R.T. Frost, Deposition of polycrystalline silicon films on metal substrates under ultra-high vacuum 47 (1979) 384
Radoń, T. and Z. Sidorski, Adsorption and condensation of bismuth on tungsten 47 (1979) 115
Rasmussen, S.E., see Jørgensen 47 (1979) 124
Reichelt, K., see Lampert 47 (1979) 77
Revcolevschi, A., see Berthon 47 (1979) 736
Rijks, H.J., J. Bloem and L.J. Giling, The effect of trace amounts of oxygen on the HCl etching of silicon 47 (1979) 397
Riley, N. and D.A. Sweet, Effects of rotation on Czochralski crystal growth 47 (1979) 557
Ristić, R.I., see Davey 47 (1979) 1
Robert, M.C., see Lefaucheux 47 (1979) 313
Robertson, J.M., see Bartels 47 (1979) 414
Robertson, J.M., see Damen 47 (1979) 486
Rodriguez, R., M. Aguiló and J. Tejada, Unstable growth of ADP crystals 47 (1979) 518
Roksnoer, P.J., see Kuiken 47 (1979) 29
Roland, G.W., see Isaacs 47 (1979) 712
Romanowski, Z., see Sokołowski 47 (1979) 421
Rosenberger, F., see Abernathey 47 (1979) 145
Rosenberger, F., J.M. Olson and M.C. Delong, A gas handling system for exacting crystal growth preparations 47 (1979) 321
Roy, B.N. and V.K. Handa, Kinetics of crystallization of barium tunstate from solutions in sodium tungstate melts by continuous cooling 47 (1979) 577
Ruckenstein, E., Role of wetting in sintering and redispersion of supported metal crystallites 47 (1979) 666

Rusek, A., see Sokołowski 47 (1979) 421
Russell, G.J. and J.Woods, Vapour growth and defect characterisation of large single crystals of ZnS and Zn(Se, Se) 47 (1979) 647

Sachs, E.M., In-situ carbon–silicon ribbon thermocouple 47 (1979) 477
Saito, Y., Crystal structure and habit of silicon and germanium particles grown in argon gas 47 (1979) 61
Saitoh, T., see Kuroda 47 (1979) 251
Sakaguchi, K., see Osaka 47 (1979) 527
Sakata, T., see Kojima 47 (1979) 589
Sakudo, T., see Oka 47 (1979) 568
Sarig, S., C.L. Leci and N. Eidelman, Agglomeration of potassium chloride crystals from supersaturated aqueous solutions 47 (1979) 365
Satoh, J., see Osaka 47 (1979) 527
Sekiguchi, Y., H. Funakubo et G. Champier, Observation en microscopie électronique à balayage des faces de croissance *Z* du quartz synthétique 47 (1979) 751
Sekiya, T. and H. Okuda, Flux growth of $Cr_2O_3$ crystals from a $K_2Cr_2O_7$–$K_2CrO_4$–$K_2B_4O_7$ mixture 47 (1979) 551
Sharkhatunyan, R.O., see Nalbandyan 47 (1979) 427
Shaw, D.W., Morphology analysis in localized crystal growth and dissolution 47 (1979) 509
Shibata, N., see Iwanaga 47 (1979) 703
Shimada, S., see Ito 47 (1979) 310
Shinohara, K., see Yoshikawa 47 (1979) 230
Shlichta, P.J., see Chen 47 (1979) 43
Shtrikman, H., see Tamari 47 (1979) 463
Sidorski, Z., see Radoń 47 (1979) 115
Singh, G., see Singh 47 (1979) 755
Singh, S.R. and G. Singh, The occurrence of high period polytype of SiC at the interface of two interacting spirals 47 (1979) 755
Smith, S.H. and P.J. Walker, The growth of $LaAlO_3$ crystals enriched in isotope $^{17}O$ 47 (1979) 315
Sokołowska, A., see Sokołowski 47 (1979) 421
Sokołowski, M., A. Sokołowska, B. Gokieli, A. Michalski, A. Rusek and Z. Romanowski, Reactive pulse plasma crystallization of diamond and diamond-like carbon 47 (1979) 421
Spear, K.E., see Brun 47 (1979) 335
Steyn, J.B., see Barter 47 (1979) 623
Sunagawa, I., see Hosoya 47 (1979) 93
Sweet, D.A., see Riley 47 (1979) 557

Tadano, H., see Nishizawa 47 (1979) 434
Takahashi, T., H. Itoh and A. Takeuchi, Chemical vapor deposition of hexagonal boron nitride thick film or iron 47 (1979) 245
Takebe, H., see Fujita 47 (1979) 326
Tamari, N. and H. Shtrikman, Improved nucleation and a planar interface in LPE grown $Pb_{1-x}Sn_xTe$ heterostructures 47 (1979) 463
Tanaka, T., see Yajima 47 (1979) 493
Tejada, J., see Rodriguez 47 (1979) 518
Terashima, K., Low-defect InSb crystal growth by InN doping 47 (1979) 746
Thorpe, B.W., see Parry 47 (1979) 541
Touzelin, B., see Berthon 47 (1979) 736
Treivus, E.B., see Hodorowicz 47 (1979) 573
Trivedi, R., H. Franke and R. Lacmann, Effects of interface kinetics on the growth rate of dendrites 47 (1979) 389
Tsunashima, A., see Ito 47 (1979) 310
Tsutsumi, M., see Ohta 47 (1979) 135

Ueda, R., see Yoshikawa 47 (1979) 230
Ueno, S., see Ohta 47 (1979) 135
Unoki, H., see Oka 47 (1979) 568

Van der Eerden, J.P., see Van Enckevort 47 (1979) 501

Van der Linden, W.H., see Van Enckevort 47 (1979) 196
Van der Putte, P., L.J. Giling and J. Bloem, Surface morphology of HCl etched silicon wafers. III. The origin of etch pits 47 (1979) 437
Vaněk, P. and S. Kadečková, Growth striations in Fe-3Wt%Si single crystals grown by floating zone melting at various growth rates 47 (1979) 458
Van Enckevort, W.J.P. and W.H. van der Linden, On the relation between etch pits or growth hillocks and dislocations on the (111) faces of potassium aluminium alum 47 (1979) 196
Van Enckevort, W.J.P. and J.P. van der Eerden, Monte Carlo simulation of a (111) diamond face around the roughening transition 47 (1979) 501
Van Rosmalen, G.M., see Christoffersen 47 (1979) 607
Van Run, A.M.J.G., Computation of stiated impurity distributions in melt-grown crystals, taking account of periodic remelt 47 (1979) 680
Van Wormer, K.A., see Viola 47 (1979) 127
Venkateswara Rao, A., see Patel 47 (1979) 213
Viola, M.S., K.A. Van Wormer and G.D. Botsaris, A new technique for simulating two-dimensional nucleation models of crystal growth 47 (1979) 127

Walker, P.J., see Smith 47 (1979) 315
Walker, P.J., Crystal growth of sodium sulphide, $Na_2S$ 47 (1979) 598
Wanklyn, B.M., see Garrard 47 (1979) 159
Wernick, J.H., G.W. Hull, T.H. Geballe, J.E. Bernardini and E. Buehler, Czochralski growth of A15 structure intermetallic compounds 47 (1979) 73
Whitehouse, C.R. and A.A. Balchin, Polytypism in tin disulphide 47 (1979) 203
Wilcox, W.R., see Chen 47 (1979) 43
Wilkins, C.W. and G.P. Gill, The preparation of low defect density LPE garnet films for magnetic bubble device fabrication 47 (1979) 299
Wilson, W.S., see Parker 47 (1979) 5
Woods, J., see Cutter 47 (1979) 405
Woods, J., see Russell 47 (1979) 647

Yacamán, M.J., see Heinemann 47 (1979) 177
Yacamán, M.J., K. Heinemann, C.Y. Yang and H. Poppa, The structure of small, vapor-deposited particles. II. Experimental study of particles with hexagonal profile 47 (1979) 187
Yacamán, M.J., see Yang 47 (1979) 283
Yajima, F., T. Tanaka, E. Bannai and S. Kawai, Preparation of $TiC_x$ single crystal with homogeneous compositions 47 (1979) 493
Yamada, T., see Nakano 47 (1979) 693
Yamaguchi, T., see Iwanaga 47 (1979) 703
Yang, C.Y., see Heinemann 47 (1979) 177
Yang, C.Y., see Yacamán 47 (1979) 187
Yang, C.Y., Crystallography of decahedral and icosahedral particles. I. Geometry of twinning 47 (1979) 274
Yang, C.Y., M.J. Yacamán and K. Heinemann, Crystallography of decahedral and icosahedral particles. II. High symmetry orientations 47 (1979) 283
Yoneda, N., see Ito 47 (1979) 310
Yoshiie, T., see Iwanaga 47 (1979) 703
Yoshikawa, M., M. Ito, K. Shinohara and R. Ueda, Misfit dislocations in PbTe–PbSnTe heterojunction 47 (1979) 230

Zimmermann, H., see Eyer 47 (1979) 219
Žižić, B., see Davey 47 (1979) 1

## SUBJECT INDEX


Acoustic waves 712
Adatom 357, 437
Adsorption 115
Agglomeration 365
Alkali
– fluoro aluminates 699
– halides
– – low level impurity of 321
Alkaline earth
– rare earth pentaoxometallates 739
Alloys 133, 261, 317, 458, 469, 583
Aluminum
– gallium arsenide 155
Ammonium
– dihydrogen phosphate 1, 518
– fluoro aluminate 699
– fluoro ferrate 699
Anatase 139
Apparatus
– for melt growth
– – by Bridgman-Stockbarger
– – – using controlled growth furnace
– – – – of thallium vanadium sulphide 712
– – – using thermic screen translation technique
– – – – of fluorides 449
– – by Czochralski
– – – of lead monoxide 568
– – – of rare earth tetraborides 429
– – by floating zone
– – – under micro gravity
– – – – of silicon 219
– for solution growth
– – by flux
– – – of chromium (111) oxide 551
– – – of lithium neodymium metaphosphate ($LiNdP_4O_{12}$) 693
– – by low temperatures
– – – of calcite 21
– for thin film growth
– – – by vapor phase epitaxy
– – – by evaporation and condensation
– – – of cadmium sulphide 623
– – – by chemical vapor deposition
– – – – of boron nitride 245
– – – – of iridium phosphide 267
– for vapor growth
– – by zone sublimation
– – – under micro gravity
– – – – of cadmium telluride 219
– – by evaporation and condensation
– – – of zinc selenide 405
– – – of zinc sulphide 647
– – in "semiclosed" transport ampoule
– – – of iodine 145
– for miscellaneous purposes
– – for gas purification and ampoule filling 321
– – for observing thermal convection and fluid motion 109
– – for schlieren observation of convection 43
– – for space crystallization, using elliptical mirror furnaces 219
– – for temperature gradient measurement in LPE 619

Barium
– lead hexa-aluminate 414
– molybdate 743
– tungstate 577
Bismuth 115
– selenate $Bi_2(SeO_4)_3$ 82
Boron
– nitride 245
Boundary layer control 43
Brushite 135, 313

Cadmium
– selenide 703
– sulphide 373, 623, 703
– telluride 219
Calcite 21, 93
Calcium
– sulphate dihydrate 607
– hydrogen phosphate 135
– hydroxyapatite 671
– oxalate $xH_2O$ (weddellite) 719
Cellular growth 469
Characterization methods
– by AAS 326, 577, 739
– by birefringence studies 593
– by chemical analysis 493, 577, 699
– by convection phenomena, using schlieren observation 43
– by dielectric constant 568
– by differential scanning calorimetry (DSC) 541
– by DTA 577
– by dilatometry 5
– by electrical methods 12, 73, 267, 326, 429, 493, 601, 613
– by electron diffraction 61, 283, 467
– by electron microscopy 61, 77, 135, 139, 155, 177, 187, 245, 274, 283, 299, 317, 351, 365, 384, 414, 421, 437, 463, 527, 593, 623, 647, 659, 703, 719, 727, 746, 751

– by electron spin paramagnetic resonance 659
– by emission spectra 12, 82, 326, 467
– by EPMA 155, 159, 230, 341, 414, 429, 458, 589, 654, 659, 712, 739, 749
– by field emission patterns 115
– by infrared transmission 82, 245, 341, 421, 467, 577, 654
– by ion micro mass analysis (IMMA) 12
– by ion backscattering 583
– by interference microscopy 351, 434, 458
– by magnetic susceptibility 121, 429
– by neutron diffraction 124
– by nuclear magnetic resonance 659
– by optical absorption 130, 486, 568, 659
– by optical fluorescence 130, 351
– by optical microscopy 12, 73, 93, 121, 139, 155, 159, 196, 230, 251, 315, 326, 335, 341, 351, 384, 397, 414, 429, 434, 437, 449, 463, 518, 541, 551, 577, 635, 639, 659, 693, 699, 712, 733, 736, 739, 743, 746, 749, 755
– by photoluminescence 155
– by superconductivity 73
– by surface wave acoustic properties 712
– by X-ray techniques 29, 82, 121, 124, 130, 159, 177, 187, 203, 245, 274, 313, 326, 335, 341, 351, 384, 414, 421, 434, 463, 467, 469, 486, 493, 577, 583, 589, 598, 623, 654, 659, 693, 699, 712, 736, 739, 749, 751, 755
Chromium
– oxide ($Cr_2O_3$) 551
– silicide ($Cr_3Si$) 124
Computer simulation 85, 127, 164, 501, 680
Constitutional supercooling 251, 261
Convection 43, 109
Copper
– antimony alloy 469
– chalcopyrite (film) 235
– silicon alloy 469

Decoration 357
Dendritic growth 341, 389, 518, 639
Diamond 421, 501
Diffusional control 145, 230, 357, 405, 486, 577, 613, 680
Dislocation 1, 77, 93, 196, 230, 235, 434, 463, 533, 727, 746, 755
Dissolution 509, 607
Distribution coefficient 85, 680
DNA 639

Etching
– chemical 135, 196, 213, 230, 251, 267, 335, 341, 384, 397, 427, 437, 458, 463, 469, 509, 533, 551, 693, 699, 727, 746, 751
– electrochemical (Norr) 463
– gas phase 397, 437
– thermal 568, 699

Ferrite 486
Fluorides 449
– alkali-transition metal 159
– mixed transition metals 159

Gallium
– aluminum antimonide 100
– arsenide 12, 434, 509, 601, 613
Garnets 299
Germanium 61
Gold 177, 187
– aluminum alloy 583
Grain boundary 5, 341, 541

Heat flow control 29, 145, 341
Heterostructure 463

Ice 109, 291
Impurity 5, 12, 77, 85, 139, 251, 267, 291, 299, 315, 365, 429, 613, 680, 739, 746
Inclusions 463, 469, 518, 727
Indium
– antimonide 746
– phosphide 267
Interface 5, 12, 29, 109, 145, 230, 235, 261, 317, 434, 463, 473, 477, 501, 557, 680, 755
Intermetallic compounds 73
Iodine 145
Ionic clusters 164
Ionic conductor 659
Iron
– silicon alloy 458
– (II) oxide 736
Isotope enrichment 315

Kinetics
– of dissolution 509, 671
– of evaporation 77
– of etching 397, 437
– of growth 1, 21, 29, 43, 115, 127, 267, 291, 389, 405, 473, 509, 573, 577, 583, 623, 654, 666, 699, 743, 755
– of interface control 389
– of sublimation 703

Lanthanum
– aluminate 315
Lasers 130, 230, 351
Lattice mismatch 130, 230, 235, 351, 414, 463, 486, 527
Lead
– monoxide 568
– tin telluride 230, 379, 463
Liesegang rings 743
Lithium
– iodate 427
– metasilicate 335
– nitride 133
– titanate ($Li_2Ti_3O_4$) 659
Lutetium
– hydrous oxide 635

Magnesium
– fluoride 449
Magnetic bubbles 299

Manganese
– silicide ($Mn_{15}Si_{26}$) 589
– zinc ferrite 486
Mathematical model
– for temperature distribution 29, 219
Melt growth
– by Bridgman-Stockbarger
– – of gallium aluminum antimonide 100
– – of lithium titanate ($Li_2Ti_3O_7$) 659
– – of manganese silicide ($Mn_{15}Si_{26}$) 589
– – of sodium sulphide 598
– – of thallium vanadium sulphide 712
– – of zinc telluride 727
– – of zinc titanate 486
– – modified, using TST
– – – of fluorides 449
– by Czochralski
– – of iridium antimonide 746
– – of intermetallic compounds 73
– – of lead monoxide 568
– – of lithium metasilicate 335
– – of r.e. tetraborides 429
– – of silicon 251, 533
– – rotation of crystal and crucible 557
– by floating zone
– – of iron-silicon alloy 458
– – of silicon 29, 219
– – of titanium carbide 493
– – of trichromium silicide 124
– – by uniaxial solidification
– – of copper alloys 469
– by zone melting
– – of iron (II) oxide 736
– – theory of 85
– theory of 680
Mercury
– cadmium telluride 341, 749
MIS – field effect transistor fabrication 12
Morphological stability 261, 389, 518
Morphology of growth 61, 82, 93, 135, 155, 177, 187, 274, 283, 317, 365, 427, 463, 473, 486, 509, 518, 551, 577, 589, 639, 654, 703, 719, 739, 743, 749, 755
Morphology of etching 397, 437

Neodymium
– aluminum borate 130
Nucleation 127, 139, 177, 187, 291, 357, 437, 463, 541, 593, 743

Organic crystals 473, 593

Perfection of crystals 61, 93, 155, 196, 235, 299, 313, 434, 458, 486, 518, 533, 541, 746, 751
Phase diagrams 100, 379, 486, 493, 551, 568, 589, 693, 712, 727, 739
Phenomenological theory 5, 93, 109, 557
Piezoelectricity 335
Point defects 373
Polytypism 203, 647, 755
Potassium
– aluminum alum 196
– chloride 365
– neodymium tetraphosphate 351
– perchlorate 213
– triple nitrite 121

Quartz 93, 751

Rare earth
– tetraborides 429
Rutile 139

Schmidt number 557
Silicon 29, 61, 219, 251, 384, 397, 437, 477, 533, 680
– carbide 755
Silver
– chalcopyrite (film) 235
– selenate 467
Sodium
– alumino silicate 654
– chlorate 43
– chloride 77
– sulfide 598
Solar cells 235
Solid growth
– by hot stage microscopy
– – of TNT 541
– by recrystallization
– – of gold aluminum alloy 583
– – of mercury cadmium telluride 341
Solubility 639
Solution growth
– by flux
– – of alkaline earth, rare earth pentaoxometallates 739
– – of barium tungstate 577
– – of chromium (III) oxide 551
– – of fluorides 159
– – of lanthanum aluminate 315
– – of lithium neodymium metaphosphate 693
– – of lead monoxide 568
– – of TMTTF-TCNQ 733
– by gel
– – of barium molybdate 743
– – of bismuth selenate 82
– – of brushite 135, 313
– – of calcium oxalate 719
– – of potassium perchlorate 213
– – of silver selenate 467
– – of sodium aluminosilicate 654
– – of triple nitrites 121
– by hydrothermal
– – of alkali fluoroaluminates 699
– – of ammonium fluoroaluminate 699
– – of ammonium fluoroferrate 699

– – of quartz 751
– – of thallium fluoroaluminate 699
– by low temperatures
– – of alum 196
– – of ammonium dihydrogen phosphate 518
– – of calcite 21
– – of calcium sulphate dihydrate 607
– – of DNA 639
– – of lithium nitride 133
– – of lutetium hydrous oxide 635
– – of potassium chloride 365
– – of potassium neodymium tetraphosphate 351
– – of sodium chlorate 43
– – of urea 573
Space crystallization 219
Spiral growth 196
Statistical mechanics 501
Stefan problam 109
Step 77, 357, 518, 755
Stoichiometry 405
Strain 235, 477
Striations 458
Supercooling, supersaturation 43, 145, 518, 573
Surface energy, determination of 501
Surface processes, theory 373, 437, 501
Surface structure 77, 196, 274, 283, 373, 501, 518, 613, 666, 719, 751

Tellurium 593
Thallium
– fluoroaluminate 699
– triple nitrite 121
– vanadium sulphide 712
Thermocouple 477
Thermodynamics 100, 139, 164, 261, 397, 405, 437, 607, 623, 666
Thin film growth
– by liquid phase epitaxy
– – of aluminum gallium arsenide 155
– – of barium lead hexaluminate 414
– – of ferrite (manganese-zinc) 486
– – of gallium aluminum antimonide 100
– – of gallium arsenide 434
– – of garnets 299
– – of lead tin telluride 230, 463
– – of neodymium aluminum borate 130
– by vapor phase epitaxy
– – by chemical vapor deposition
– – – of boron nitride 245
– – – of gallium arsenide 12, 601, 613
– – – of iridium phosphide 267
– – by evaporation and condensation
– – – of cadmium sulphide 623
– – – of gold 357
– – – of organic crystals 593
– – – of potassium neodymium tetraphosphate 351
– – – of silicon 384
– – – of tellurium 593
– – – of tin 527
– – by pulse plasma, reduced pressure
– – – of diamond 421
Tin 527
– disulphide 203
Titanium
– carbide 493
– dioxide 139, 321
– gold ($Ti_3Au$) 73
TMTTF-TCNQ 733
TNT 5, 541
Twinning 93, 187, 274, 639, 647

Urea 573

Vanadium
– germanide ($V_3Ge$) 73
– silicide ($V_3Si$) 73
Vapor growth
– by chemical transport
– – of gallium arsenide 12
– – of manganese silicide ($Mn_{15}Si_{26}$) 589
– – of mercury cadmium telluride 749
– – of tin disulphide 203
– – of titanium dioxide 139, 321
– – of zinc chalcogenides 326
– – of zinc germanate 310
– – using special gas system for materials purification 321
– by evaporation and condensation
– – of bismuth 115
– – of cadmium chalcogenide 703
– – of chromium (III) oxide 551
– – of germanium 61
– – of gold 177
– – of silicon 61, 384
– – of zinc oxide 703
– – of zinc selenide 405
– – of zinc sulphide 647, 703
– – in "semiclosed" ampoule
– – – of iodine 145
– – theory of 405
– by sputtering (magnetron)
– – of zinc oxide 171
– by zone sublimation
– – of cadmium telluride 219

Whisker growth
– of zinc germanate 310
Wustite 736

Yttrium
– iron garnet, rare earths and germanium doped 299

Zinc
– chalcogenides 326
– germanate 310
– oxide 171, 703
– selenide 405
– sulphide 647, 703
– telluride 727
– titanate 586